

TOSHIBA INFRARED LED GaAs INFRARED EMITTER

## TLN103A

INFRARED LED FOR PHOTSENSORS

Unit : mm

OPTO-ELECTRONIC SWITCHES

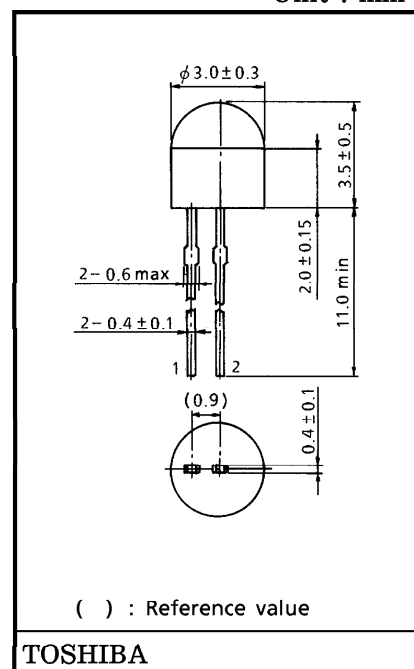
SELECTORS

TAPE AND CARD READERS

EQUIPMENT USING INFRARED TRANSMISSION

- Wide half-angle value :  $\theta_{\frac{1}{2}} = \pm 80^\circ$  (typ.)
- Excellent radiant-intensity linearity. Modulation by pulse operation and high frequency is possible.
- Same external shape as TPS603A phototransistors
- Maximum distance when used as photosensor :
 

}	When TPS603A $I_L \approx 100 \mu\text{A}$
with DC drive $\approx 5 \text{ mm}$	
with pulse drive $\approx 30 \text{ mm}$	



Weight : 0.08 g (typ.)

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Forward Current	$I_F$	60	mA
Pulse Forward Current (Note)	$I_{FP}$	1	A
Reverse Voltage	$V_R$	5	V
Forward Current Derating ( $T_a > 25^\circ\text{C}$ )	$\Delta I_F / ^\circ\text{C}$	-0.8	mA / $^\circ\text{C}$
Operating Temperature Range	$T_{opr}$	-20~75	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-30~100	$^\circ\text{C}$

PIN CONNECTION



1. Anode
2. Cathode

(Note) : Pulse width  $\leq 100 \mu\text{s}$ , repetitive frequency = 100 HzOPTICAL AND ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

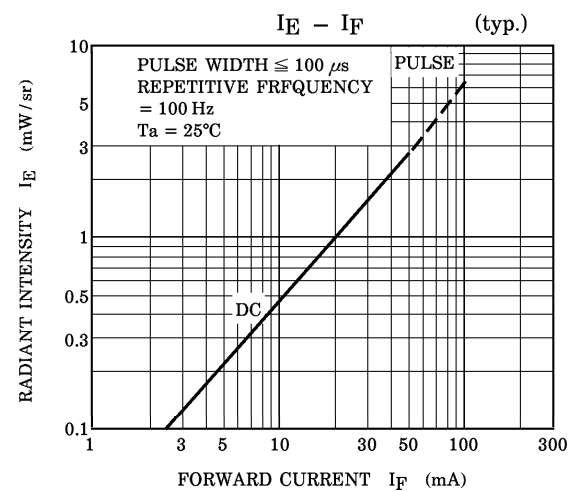
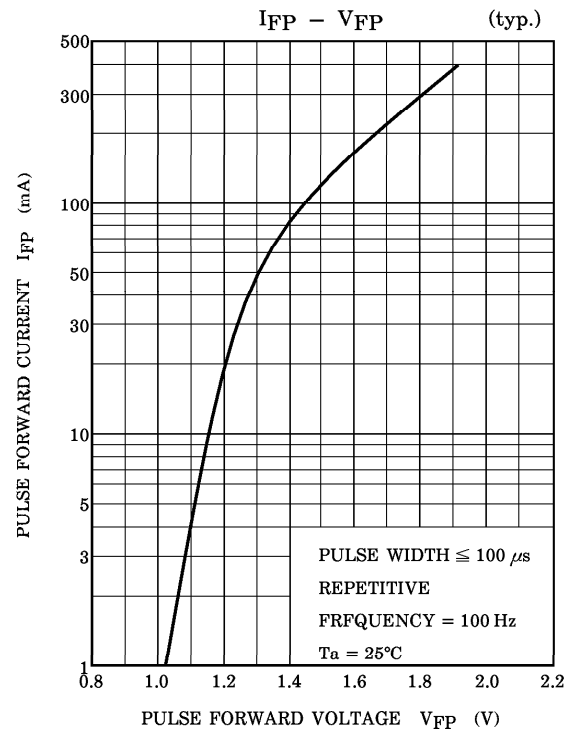
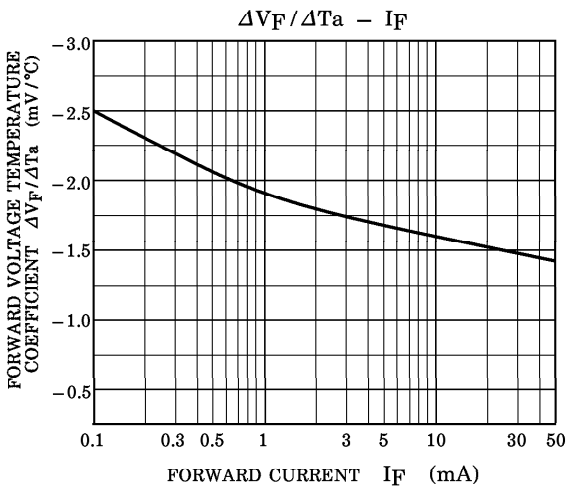
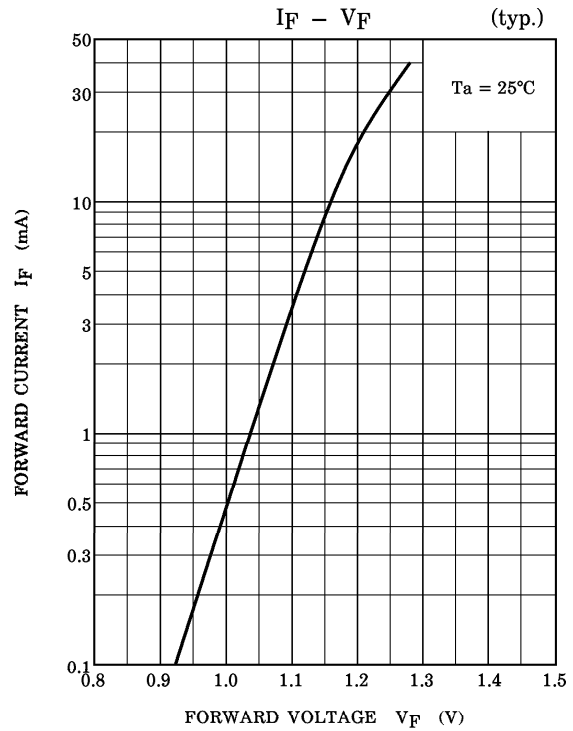
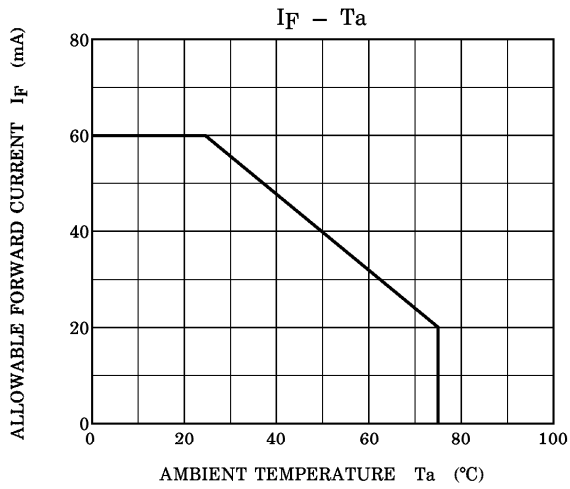
CHARACTERISTIC	SYMBOL	TEST CONDITION	Min	Typ.	Max	UNIT
Forward Voltage	$V_F$	$I_F = 10 \text{ mA}$	1.00	1.15	1.30	V
Reverse Current	$I_R$	$V_R = 5 \text{ V}$	—	—	10	$\mu\text{A}$
Radiant Intensity	$I_E$	$I_F = 20 \text{ mA}$	0.5	1.0	—	mW / sr
Radiant Power	$P_o$	$I_F = 20 \text{ mA}$	—	2.5	—	mW
Half Value Angle	$\theta_{\frac{1}{2}}$	$I_F = 20 \text{ mA}$	—	$\pm 80$	—	$^\circ$
Capacitance	$C_T$	$V_R = 0, f = 1 \text{ MHz}$	—	30	—	pF
Peak Emission Wavelength	$\lambda_P$	$I_F = 20 \text{ mA}$	—	940	—	nm
Spectral Line Half Width	$\Delta\lambda$	$I_F = 20 \text{ mA}$	—	50	—	nm

**PRECAUTIONS**

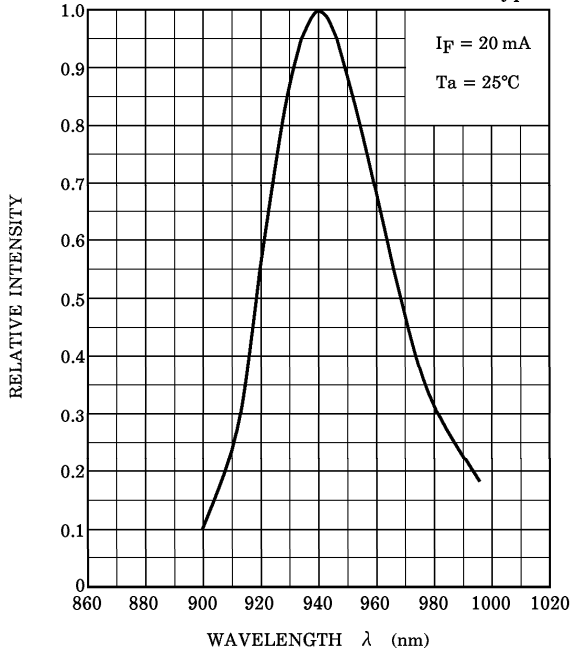
Please be careful of the followings.

1. Soldering temperature : 260°C max  
Soldering time : 3 s max  
(Soldering must be performed 2 mm from the bottom of the package.)
2. When forming the leads, bend each lead under the 2 mm from the body of the device.  
Soldering must be performed after the leads have been formed.
3. Radiation intensity falls over time due to the current which flows in the infrared LED.  
When designing a circuit, take into account this change in radiant power over time.  
The ratio of fluctuation in radiation intensity to fluctuation in optical output is 1 : 1.

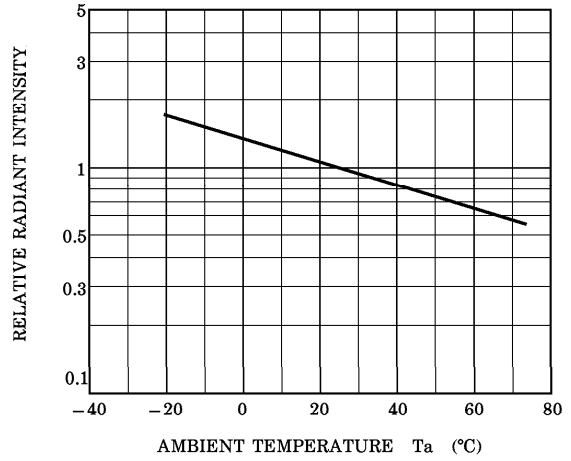
$$\frac{I_E(t)}{I_E(0)} = \frac{P_O(t)}{P_O(0)}$$



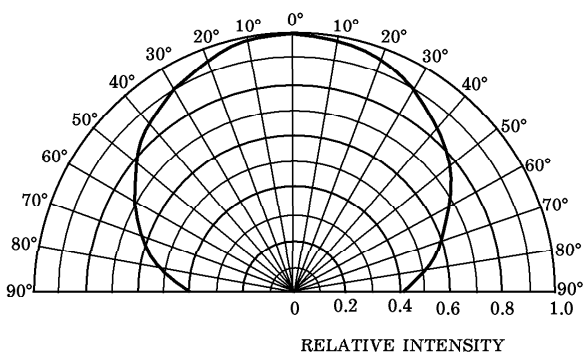
WAVELENGTH CHARACTERISTIC (typ.)



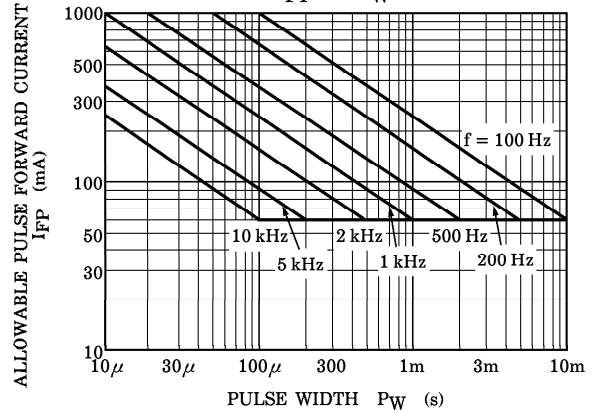
RELATIVE  $I_E - T_a$  (typ.)



RADIATION PATTERN (typ.) ( $T_a = 25^\circ\text{C}$ )



$I_{FP} - P_W$



**RESTRICTIONS ON PRODUCT USE**

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